

Masashi Arita

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96
papers

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h-index

33
g-index

117
ext. papers

1,418
ext. citations

2.6
avg, IF

4.13
L-index

#	Paper	IF	Citations
96	Giant tunneling magnetoresistance in epitaxial Co ₂ MnSi/MgO/Co ₂ MnSi magnetic tunnel junctions by half-metallicity of Co ₂ MnSi and coherent tunneling. <i>Applied Physics Letters</i> , 2012 , 101, 132418	3.4	170
95	Spin-dependent tunneling characteristics of fully epitaxial magnetic tunneling junctions with a full-Heusler alloy Co ₂ MnSi thin film and a MgO tunnel barrier. <i>Applied Physics Letters</i> , 2006 , 89, 192505	3.4	170
94	Fabrication of fully epitaxial magnetic tunnel junctions using cobalt-based full-Heusler alloy thin film and their tunnel magnetoresistance characteristics. <i>Journal Physics D: Applied Physics</i> , 2006 , 39, 824-833	3.33	80
93	In situ transmission electron microscopy analysis of conductive filament during solid electrolyte resistance switching. <i>Applied Physics Letters</i> , 2011 , 98, 212104	3.4	56
92	Switching operation and degradation of resistive random access memory composed of tungsten oxide and copper investigated using in-situ TEM. <i>Scientific Reports</i> , 2015 , 5, 17103	4.9	44
91	Filament formation and erasure in molybdenum oxide during resistive switching cycles. <i>Applied Physics Letters</i> , 2014 , 105, 173504	3.4	37
90	Thin film deposition and characterization of pure and iron-doped electron-beam evaporated tungsten oxide for gas sensors. <i>Thin Solid Films</i> , 2010 , 518, 4791-4797	2.2	37
89	Resistance switching properties of molybdenum oxide films. <i>Thin Solid Films</i> , 2012 , 520, 4762-4767	2.2	36
88	Tungsten Films with the A15 Structure. <i>Japanese Journal of Applied Physics</i> , 1993 , 32, 1759-1764	1.4	36
87	Fabrication of Fe-doped WO ₃ films for NO ₂ sensing at lower operating temperature. <i>Sensors and Actuators B: Chemical</i> , 2015 , 221, 393-400	8.5	35
86	Effect of nonstoichiometry on the half-metallic character of Co ₂ MnSi investigated through saturation magnetization and tunneling magnetoresistance ratio. <i>Physical Review B</i> , 2014 , 89,	3.3	32
85	Structural and magnetic properties of epitaxially grown full-Heusler alloy Co ₂ MnGe thin films deposited using magnetron sputtering. <i>Journal of Applied Physics</i> , 2006 , 99, 08J110	2.5	29
84	Improved tunnel magnetoresistance characteristics of magnetic tunnel junctions with a Heusler alloy thin film of Co ₂ MnGe and a MgO tunnel barrier. <i>Journal of Applied Physics</i> , 2007 , 101, 09J513	2.5	27
83	The effect of pressure and W-doping on the properties of ZnO thin films for NO ₂ gas sensing. <i>Applied Surface Science</i> , 2015 , 357, 728-734	6.7	23
82	Determination of Long-Range-Order Parameter of Fe ₃ Si Alloy by means of ⁵⁷ Fe Mössbauer Effect. <i>Transactions of the Japan Institute of Metals</i> , 1985 , 26, 710-720		23
81	Probing electrochemistry at the nanoscale: in situ TEM and STM characterizations of conducting filaments in memristive devices. <i>Journal of Electroceramics</i> , 2017 , 39, 73-93	1.5	22
80	I-V measurement of NiO nanoregion during observation by transmission electron microscopy. <i>Journal of Applied Physics</i> , 2011 , 109, 053702	2.5	21

79	Transmission electron microscopy of La _{0.7} Ca _{0.3} MnO ₃ thin films. <i>Journal of Magnetism and Magnetic Materials</i> , 2000 , 211, 84-90	2.8	20
78	In-situ transmission electron microscopy of conductive filaments in NiO resistance random access memory and its analysis. <i>Journal of Applied Physics</i> , 2013 , 113, 083701	2.5	19
77	Smooth Interfacial Scavenging for Resistive Switching Oxide via the Formation of Highly Uniform Layers of Amorphous TaO. <i>ACS Applied Materials & Interfaces</i> , 2018 , 10, 5609-5617	9.5	16
76	Preparation of resistance random access memory samples for in situ transmission electron microscopy experiments. <i>Thin Solid Films</i> , 2013 , 533, 48-53	2.2	16
75	Analysis of resistance switching and conductive filaments inside Cu-Ge-S using in situ transmission electron microscopy. <i>Journal of Materials Research</i> , 2012 , 27, 886-896	2.5	15
74	Switching of Cu/MoO _x /TiN CBRAM at MoO _x /TiN interface. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2016 , 213, 306-310	1.6	15
73	Development of TEM Holder Generating In-Plane Magnetic Field Used for In-Situ TEM Observation. <i>Materials Transactions</i> , 2014 , 55, 403-409	1.3	14
72	The Observation of Conduction Spot in NiO Resistance Random Access Memory. <i>Japanese Journal of Applied Physics</i> , 2011 , 50, 081101	1.4	14
71	Microstructural transitions in resistive random access memory composed of molybdenum oxide with copper during switching cycles. <i>Nanoscale</i> , 2016 , 8, 14754-66	7.7	13
70	Epitaxial growth of Heusler alloy Co ₂ MnSi/MgO heterostructures on Ge(001) substrates. <i>Applied Physics Letters</i> , 2011 , 98, 262505	3.4	12
69	Green Synthesis of Size-Tunable Iron Oxides and Iron Nanoparticles in a Salt Matrix. <i>ACS Sustainable Chemistry and Engineering</i> , 2019 , 7, 17697-17705	8.3	10
68	Microstructure and electric property of MgO/Fe/MgO tri-layer films forming a nano-granular system. <i>Microelectronic Engineering</i> , 2008 , 85, 2445-2450	2.5	10
67	Multifunctional Device Using Nanodot Array. <i>Japanese Journal of Applied Physics</i> , 2006 , 45, 5317-5321	1.4	10
66	Tip production technique to form ferromagnetic nanodots. <i>Materials Science and Engineering C</i> , 2003 , 23, 927-930	8.3	10
65	Structural and electromagnetic characterizations of FeBrF ₂ granular films. <i>Journal Physics D: Applied Physics</i> , 2006 , 39, 5103-5108	3	9
64	In situ Conductance Measurement of a Limited Number of Nanoparticles during Transmission Electron Microscopy Observation. <i>Japanese Journal of Applied Physics</i> , 2005 , 44, L790-L792	1.4	9
63	The electron-density distribution and chemical bonding of A15-type Cr obtained by the maximum-entropy method. <i>Journal of Physics Condensed Matter</i> , 1994 , 6, 8681-8690	1.8	9
62	The Observation of Conduction Spot in NiO Resistance Random Access Memory. <i>Japanese Journal of Applied Physics</i> , 2011 , 50, 081101	1.4	9

61	(Invited) Visualization of Conductive Filament of ReRAM during Resistive Switching by in-situ TEM. <i>ECS Transactions</i> , 2015 , 69, 299-309	1	8
60	Single-Electron Device With Si Nanodot Array and Multiple Input Gates. <i>IEEE Nanotechnology Magazine</i> , 2009 , 8, 535-541	2.6	8
59	Crystal structures and light absorption spectra of 1,4-dithioketo-3,6-diphenyl-pyrrolo-[3,4-c]-pyrrole. <i>Journal of Applied Physics</i> , 1991 , 70, 4065-4072	2.5	8
58	Highly Spin-Polarized Tunneling in Epitaxial Magnetic Tunnel Junctions with a Co ₂ MnSi Electrode and a MgO Barrier with Improved Interfacial Structural Properties. <i>Japanese Journal of Applied Physics</i> , 2012 , 51, 093004	1.4	7
57	Tunnel current measurement of MgO and MgO/Fe/MgO nanoregions during TEM observation. <i>Superlattices and Microstructures</i> , 2008 , 44, 633-640	2.8	7
56	Visualization of Conductive Filament during Write and Erase Cycles on Nanometer-Scale ReRAM Achieved by In-Situ TEM 2015 ,		6
55	Fabrication of double-dot single-electron transistor in silicon nanowire. <i>Thin Solid Films</i> , 2010 , 518, S186-S189		6
54	A new crystal structure of 3,6-diphenylpyrrolo[3,4-c]pyrrole-1,4-dithione. <i>Acta Crystallographica Section C: Crystal Structure Communications</i> , 1991 , 47, 1952-1956		6
53	Crystal structure of the ordered Nb ₁₀ Ge ₇ phase. <i>Journal of Solid State Chemistry</i> , 1990 , 84, 386-400	3.3	6
52	Observation of Conductive Filament in CBRAM at Switching Moment. <i>ECS Transactions</i> , 2017 , 80, 895-902		5
51	Fabrication and single-electron-transfer operation of a triple-dot single-electron transistor. <i>Journal of Applied Physics</i> , 2015 , 118, 214305	2.5	5
50	In Situ TEM Observation of Cu/MoOx ReRAM Switching. <i>ECS Transactions</i> , 2013 , 58, 19-25	1	5
49	Silicon nanodot-array device with multiple gates. <i>Materials Science in Semiconductor Processing</i> , 2008 , 11, 175-178	4.3	5
48	Morphological study of Cr smoke particles with A15 structure. <i>Philosophical Magazine A: Physics of Condensed Matter, Structure, Defects and Mechanical Properties</i> , 2001 , 81, 1597-1612		5
47	Surface magnetic structure of epitaxial magnetite thin films grown on MgO(001). <i>Journal of Applied Physics</i> , 2009 , 105, 07D545	2.5	4
46	Conductance measurements of nanoscale regions with in situ transmission electron microscopy. <i>Materials Science and Engineering C</i> , 2006 , 26, 776-781	8.3	4
45	Smoke particles of ytterbium and its oxides. <i>Journal of Crystal Growth</i> , 1993 , 132, 71-81	1.6	4
44	Structure images of the hexagonal Nb ₅ Ge ₃ (D88) structure. <i>Physica Status Solidi A</i> , 1985 , 88, K1-K4		4

43	Coupling capacitance between double quantum dots tunable by the number of electrons in Si quantum dots. <i>Journal of Applied Physics</i> , 2015 , 117, 084316	2.5	3
42	Stable and Tunable Current-Induced Phase Transition in Epitaxial Thin Films of CaRuO. <i>ACS Applied Materials & Interfaces</i> , 2020 , 12, 28368-28374	9.5	3
41	Fabrication and evaluation of series-triple quantum dots by thermal oxidation of silicon nanowire. <i>AIP Advances</i> , 2015 , 5, 117144	1.5	3
40	(Invited) High-Speed Operation of Si Single-Electron Transistor. <i>ECS Transactions</i> , 2013 , 58, 73-80	1	3
39	Single-electron transistor properties of FeBrF2 granular films. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2008 , 147, 100-104	3.1	3
38	Magnetic microstructure of NiFe/Cu/NiFe films observed by Lorentz microscopy. <i>Journal of Electron Microscopy</i> , 1999 , 48, 595-600		3
37	Transmission electron microscopy of La _{0.7} Ca _{0.3} MnO ₃ CMR films. <i>Journal of Electron Microscopy</i> , 1999 , 48, 381-385		3
36	DEFECTS OF A15 SMALL PARTICLES IN TUNGSTEN THIN FILMS. <i>Surface Review and Letters</i> , 1996 , 03, 1191-1194	1.1	3
35	Electron microscopy of phase boundaries between the A15 and D8m, structures of Nb-ge. <i>Philosophical Magazine Letters</i> , 1989 , 60, 161-169	1	3
34	Initial states and analog switching behaviors of two major tantalum oxide resistive memories. <i>Japanese Journal of Applied Physics</i> , 2020 , 59, 044004	1.4	2
33	Tunnel magnetocapacitance in Fe/MgF ₂ single nanogranular layered films. <i>Applied Physics Letters</i> , 2020 , 116, 082401	3.4	2
32	In-situ Electron Microscopy of Cu Movement in MoO _x /Al ₂ O ₃ Bilayer CBRAM during Cyclic Switching. <i>ECS Transactions</i> , 2017 , 80, 903-910	1	2
31	Single-electron device using Si nanodot array and multi-input gates 2006 ,		2
30	Molecular Orientations of 1,4-dithioketo-3,6-diphenyl-pyrrolo-[3,4-c]-pyrrole on Crystalline Substrates. <i>Japanese Journal of Applied Physics</i> , 1993 , 32, 2842-2853	1.4	2
29	Full Adder Operation Based on Si Nanodot Array Device with Multiple Inputs and Outputs. <i>International Journal of Nanotechnology and Molecular Computation</i> , 2009 , 1, 58-69		2
28	Periodic Coulomb blockade oscillations observed in single-layered Fe nanodot array. <i>Thin Solid Films</i> , 2020 , 704, 138012	2.2	2
27	Analog memory characteristics of 1T1R MoO _x resistive random access memory 2016 ,		2
26	Filamentary switching of ReRAM investigated by in-situ TEM. <i>Japanese Journal of Applied Physics</i> , 2020 , 59, SG0803	1.4	1

25	EELS Analysis of Oxygen Scavenging Effect in a Resistive Switching Structure of Pt/Ta/SrTiO ₃ /Pt. <i>MRS Advances</i> , 2018 , 3, 1925-1930	0.7	1
24	In Situ Transmission Electron Microscopy for Electronics 2015 ,		1
23	Real-time resistive switching of Cu/MoO _x ReRAM observed in transmission electron microscope 2014 ,		1
22	High-frequency properties of Si single-electron transistor 2012 ,		1
21	Microstructure of Fe/Cu (Au) artificial superlattice. <i>Thin Solid Films</i> , 1998 , 318, 180-185	2.2	1
20	Magnetoresistance of FeBrF ₂ single-electron devices with a current-in-plane geometry. <i>Superlattices and Microstructures</i> , 2008 , 44, 449-456	2.8	1
19	Epitaxial growth of Fe nanodots on SrF ₂ /Si (111). <i>Materials Science and Engineering C</i> , 2006 , 26, 1146-1150	3.0	1
18	Electron microscopy of grain boundaries of Nb ₃ Ge with the A15 structure. <i>Physica Status Solidi A</i> , 1996 , 157, 379-392		1
17	In-situ TEM of Nanoscale ReRAM Devices. <i>Vacuum and Surface Science</i> , 2018 , 61, 766-771	0	1
16	Charge-offset stability of single-electron devices based on single-layered Fe nanodot array. <i>AIP Advances</i> , 2021 , 11, 035230	1.5	1
15	Capacitance evaluation of compact silicon triple quantum dots by simultaneous gate voltage sweeping. <i>Journal of Applied Physics</i> , 2016 , 120, 234502	2.5	1
14	Controlled Current Transport in Pt/Nb:SrTiO ₃ Junctions via Insertion of Uniform Thin Layers of TaO _x . <i>Physica Status Solidi - Rapid Research Letters</i> , 2019 , 13, 1900136	2.5	0
13	Effect of Arrangement of Input Gates on Logic Switching Characteristics of Nanodot Array Device. <i>IEICE Transactions on Electronics</i> , 2012 , E95.C, 865-870	0.4	0
12	Initialization process of Cu-based WO _x conductive bridge RAM investigated via in situ transmission electron microscopy. <i>Japanese Journal of Applied Physics</i> , 2020 , 59, S11E01	1.4	
11	EELS Analysis of Oxygen Scavenging Effect in a Resistive Switching Structure of Pt/Ta/SrTiO ₃ /Pt □ CORRIGENDUM. <i>MRS Advances</i> , 2018 , 3, 2075-2075	0.7	
10	Multifunctional Logic Gate by Means of Nanodot Array with Different Arrangements. <i>Journal of Nanomaterials</i> , 2013 , 2013, 1-7	3.2	
9	Si Nanodot Device Fabricated by Thermal Oxidation and their Applications. <i>Key Engineering Materials</i> , 2011 , 470, 175-183	0.4	
8	In-situ transmission electron microscopy observation of electromigration in Au thin wires. <i>Journal of Nanoscience and Nanotechnology</i> , 2012 , 12, 8741-5	1.3	

- 7 Phase boundaries between A15 and D88 structures of the Nb-Ge compound system. *Philosophical Magazine A: Physics of Condensed Matter, Structure, Defects and Mechanical Properties*, **1993**, 67, 1129-1141
- 6 Full Adder Operation Based on Si Nanodot Array Device with Multiple Inputs and Outputs 131-139
- 5 Probing Electrochemistry at the Nanoscale: In Situ TEM and STM Characterizations of Conducting Filaments in Memristive Devices. *Kluwer International Series in Electronic Materials: Science and Technology*, **2022**, 87-120
- 4 In situ Transmission Electron Microscopy on the Conductance Quantization of a Fe Nano-particle System. *Materia Japan*, **2005**, 44, 990-990 0.1
- 3 Tungsten and Chromium Having the A15-Structure. *Springer Series in Cluster Physics*, **1999**, 285-294
- 2 Investigation on Switching Operation in Resistive RAM Using In-Situ TEM. *Springer Proceedings in Physics*, **2017**, 205-214 0.2
- 1 Initial electrical properties of tantalum oxide resistive memories influenced by oxygen defect concentrations. *Japanese Journal of Applied Physics*, **2021**, 60, SCCE03 1.4